toward said channel region and being lower in impurity concentration and shallower in depth than said low resistivity region;

a first impurity doped layer of a first conductivity type formed in said channel region between the source/drain diffusion layers;

a second impurity doped layer of a second conductivity type formed under said first impurity doped layer; and

a third impurity doped layer of the first conductivity type formed under said second impurity doped layer, wherein

said three impurity doped layers make up a multilayer lamination structure with two junctions therebetween, wherein

said first impurity doped layer is equal to or less in junction depth than the extension region of each of said source/drain diffusion layers, and wherein

said second impurity doped layer is determined in impurity concentration and thickness to ensure that this layer is fully depleted due to a built-in potential creatable between said first and third impurity doped layers.

Please see the attached Appendix for the changes made to effect the above claims.

IN THE ABSTRACT OF THE DISCLOSURE:

Please replace the Abstract of the Disclosure with the following new abstract which is also provided on a separate sheet as required.

In a semiconductor device, source/drain layers have a low resistivity region and an extension region extending from the low resistivity region toward the channel region. The extension regions are lower in impurity concentration and shallower in depth than the low resistivity regions. The device also has a first impurity-doped layer formed in the channel region between the source/drain layers, a second impurity-doped layer formed under the first impurity-doped layer, and a third impurity-doped layer formed under the second impurity-doped layer. The first impurity-doped layer is equal or less in junction depth than the extension regions. The second impurity doped layer has impurity concentration and thickness to be fully depleted due to a built-in potential as created between the first and third impurity-doped layers.

Please see the attached Appendix for the changes made to effect the above Abstract.